

Quarterly Reliability Monitoring Results

Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier Nexperia B.V.		User Part Number						
		PDTC123EM						
Name of Laboratory		Part Description						
		Nexperia DHAM	Small Signal E	Bipolar Transist	tor			
Assembly reliability labs		MCD package						
Based on AEC-Q101 Test		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
	TEST							
# E1	Pre- and Post-Stress Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
# LI		IESD22-A113	IV/A	See below	an parts	See Delow		
		Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	208	16640	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
		Tj = Tjmax, Vr = 100% of max. datasheet						
# B1	Bias	reverse voltage	1000 hours	202	16160	0		
	тс	JECD33 A104						
# A4	Temperature Cycling	JESD22-A104 -65 °C to Timax, not to exceed 150°C	1000 cycles	52	4160	0		
# A4	remperature eyemig	JESD22-A102	1000 Cycles	32	4100	0		
	AC	Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)	96 hours	52	4160	0		
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of						
# A2 alt	Temperature Reverse Bias	rated reverse voltage ^[1]	1000 hours	52	4160	0		
		MIL-STD-750 Method 1037						
	IOL	ton = toff, devices powered to insure ΔTj =						
# A5	Intermittent Operating Life	100 °C for 15000 cycles	1000 hours	52	4160	0		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat		10 s		n 2	2.2		
# 00	SD	200 0 2 3 0	10.5	n.a.	n.a.	n.a.		
# C10	Solderability	J-STD-002		111	1110	0		
,, CIO				***	-110	•		

^[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)
Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	16160	0	0.26	3.81E+09

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